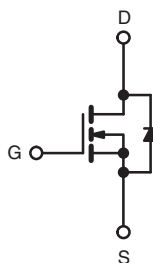
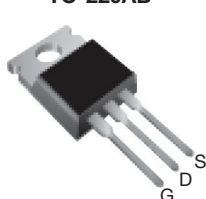


## Power MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	900	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$	8.0
$Q_g$ (Max.) (nC)	38	
$Q_{gs}$ (nC)	4.7	
$Q_{gd}$ (nC)	21	
Configuration	Single	

**TO-220AB**


N-Channel MOSFET

### FEATURES

- Dynamic  $dV/dt$  Rating
- Repetitive Avalanche Rated
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC



Available

**RoHS\***  
COMPLIANT

### DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost of the TO-220AB contribute to its wide acceptance throughout the industry.

### ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	IRFBBF20PbF SiHFBF20-E3
SnPb	IRFBBF20 SiHFBF20

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V <sub>DS</sub>	900	V
Gate-Source Voltage			V <sub>GS</sub>	± 20	
Continuous Drain Current	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C	I <sub>D</sub>	1.7	A
		T <sub>C</sub> = 100 °C		1.1	
Pulsed Drain Current <sup>a</sup>			I <sub>DM</sub>	6.8	
Linear Derating Factor				0.43	W/°C
Single Pulse Avalanche Energy <sup>b</sup>			E <sub>AS</sub>	180	mJ
Repetitive Avalanche Current <sup>a</sup>			I <sub>AR</sub>	1.7	A
Repetitive Avalanche Energy <sup>a</sup>			E <sub>AR</sub>	5.4	mJ
Maximum Power Dissipation	T <sub>C</sub> = 25 °C		P <sub>D</sub>	54	W
Peak Diode Recovery dV/dt <sup>c</sup>			dV/dt	1.5	V/ns
Operating Junction and Storage Temperature Range			T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s			300 <sup>d</sup>	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

#### Notes

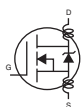
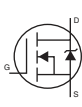
- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50\text{ V}$ , starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 117\text{ mH}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 1.7\text{ A}$  (see fig. 12).
- $I_{SD} \leq 1.7\text{ A}$ ,  $dI/dt \leq 70\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq 600$ ,  $T_J \leq 150\text{ }^\circ\text{C}$ .
- 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

**THERMAL RESISTANCE RATINGS**

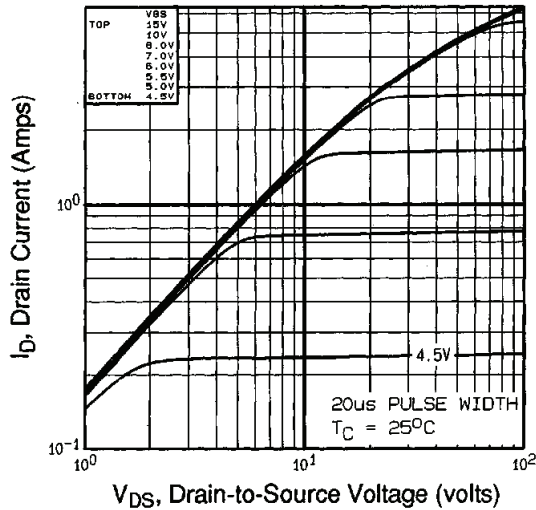
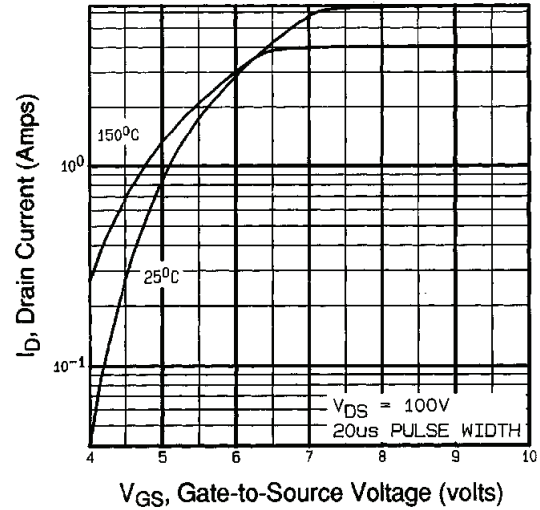
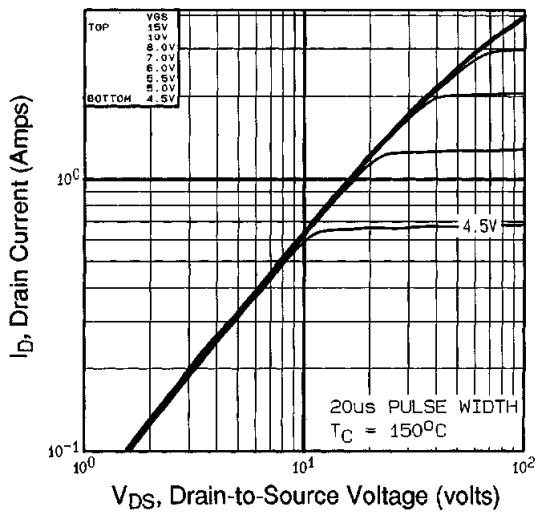
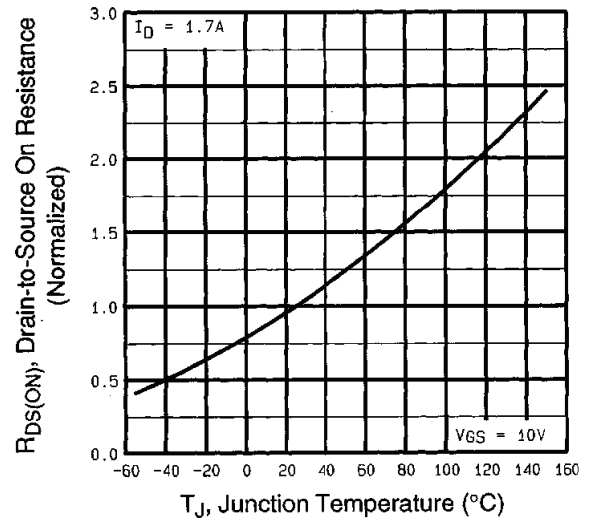
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	$R_{thCS}$	0.50	-	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	2.3	

**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		900	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	Reference to 25 °C, I <sub>D</sub> = 1 mA		-	1.1	-	V/°C
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		2.0	-	4.0	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 900 V, V <sub>GS</sub> = 0 V		-	-	100	μA
		V <sub>DS</sub> = 720 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C		-	-	500	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 1.0 A <sup>b</sup>	-	-	8.0	Ω
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 100 V, I <sub>D</sub> = 1.0 A		0.60	-	-	S
Dynamic							
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1.0 MHz, see fig. 5		-	490	-	pF
Output Capacitance	C <sub>oss</sub>			-	55	-	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	18	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 1.7 A, V <sub>DS</sub> = 360 V, see fig. 6 and 13 <sup>b</sup>	-	-	38	nC
Gate-Source Charge	Q <sub>gs</sub>			-	-	4.7	
Gate-Drain Charge	Q <sub>gd</sub>			-	-	21	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 450 V, I <sub>D</sub> = 1.7 A, R <sub>g</sub> = 18 Ω, R <sub>D</sub> = 280 Ω, see fig. 10 <sup>b</sup>		-	8.0	-	ns
Rise Time	t <sub>r</sub>			-	21	-	
Turn-Off Delay Time	t <sub>d(off)</sub>			-	56	-	
Fall Time	t <sub>f</sub>			-	32	-	
Internal Drain Inductance	L <sub>D</sub>	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal Source Inductance	L <sub>S</sub>			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	1.7	A
Pulsed Diode Forward Current <sup>a</sup>	I <sub>SM</sub>			-	-	6.8	
Body Diode Voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 1.7 A, V <sub>GS</sub> = 0 V <sup>b</sup>		-	-	1.5	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = 1.7 A, dI/dt = 100 A/μs		-	350	530	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			-	0.85	1.3	nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and L <sub>D</sub> )					

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).  
b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics,  $T_C = 25^\circ\text{C}$** 

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 2 - Typical Output Characteristics,  $T_C = 150^\circ\text{C}$** 

**Fig. 4 - Normalized On-Resistance vs. Temperature**

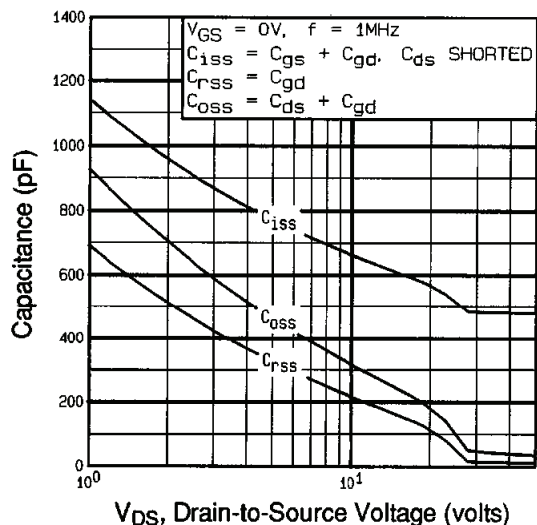


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

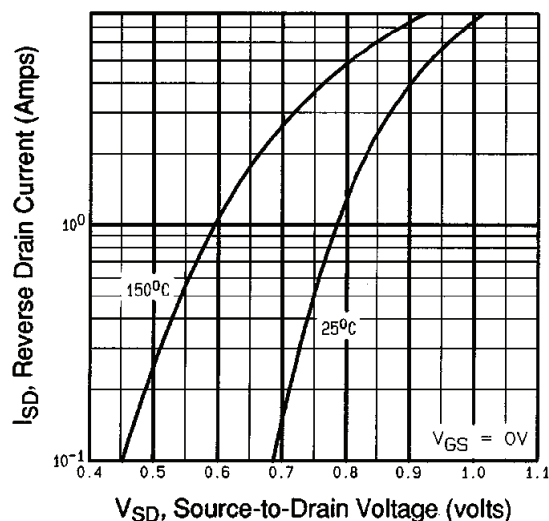


Fig. 7 - Typical Source-Drain Diode Forward Voltage

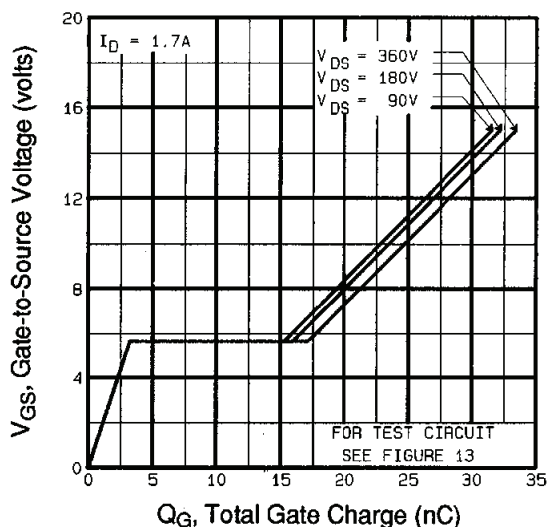


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

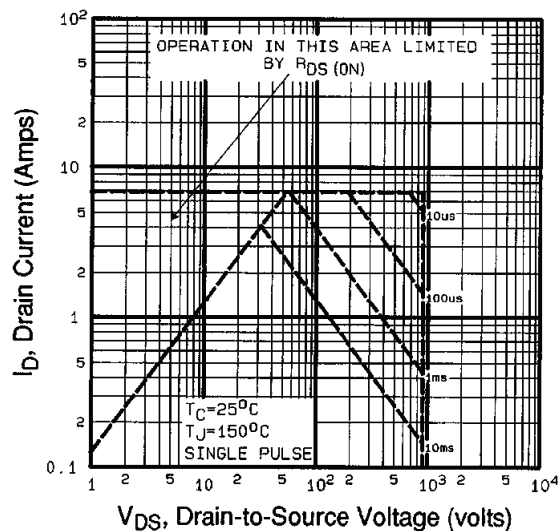


Fig. 8 - Maximum Safe Operating Area

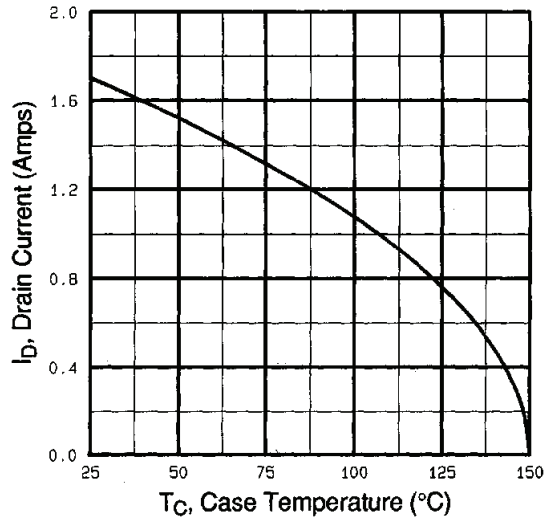


Fig. 9 - Maximum Drain Current vs. Case Temperature

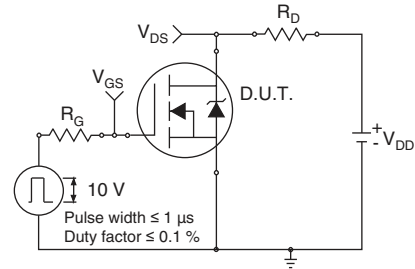


Fig. 10a - Switching Time Test Circuit



Fig. 10b - Switching Time Waveforms

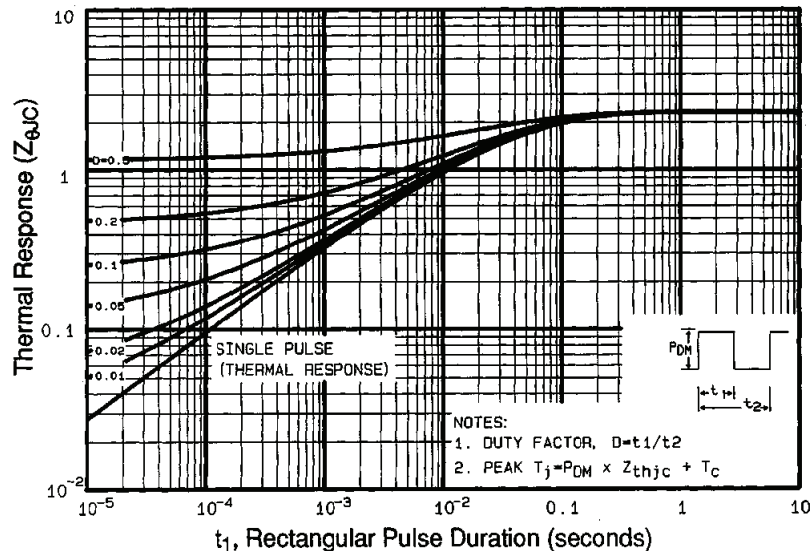


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

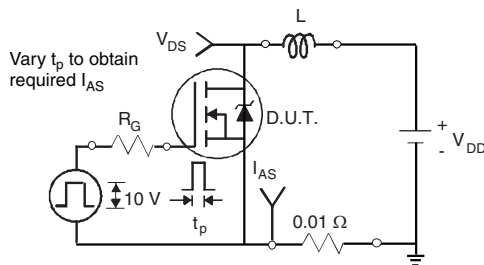


Fig. 12a - Unclamped Inductive Test Circuit

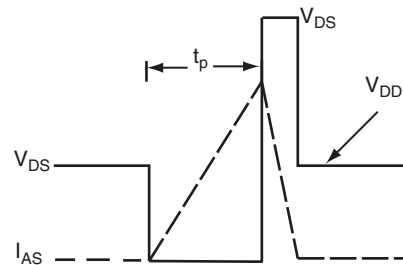


Fig. 12b - Unclamped Inductive Waveforms

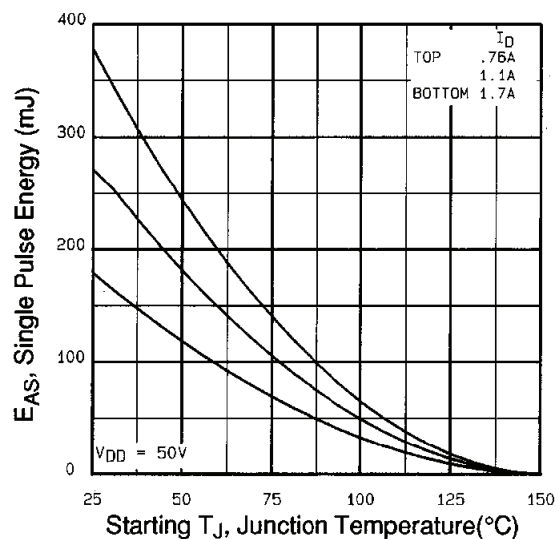


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

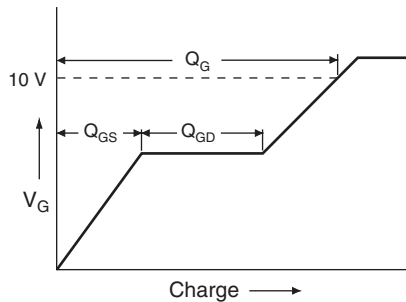


Fig. 13a - Basic Gate Charge Waveform

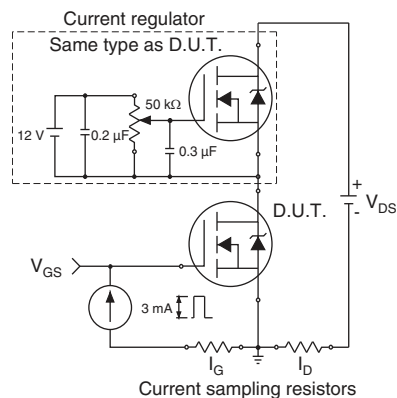
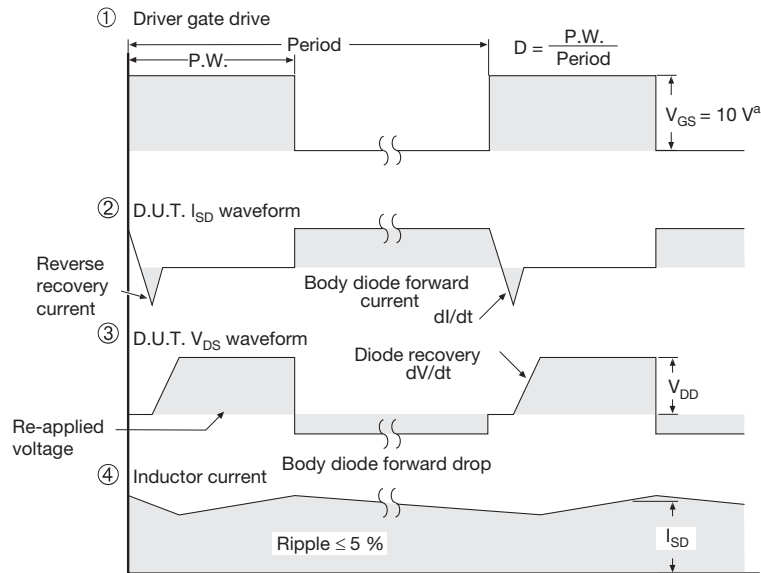
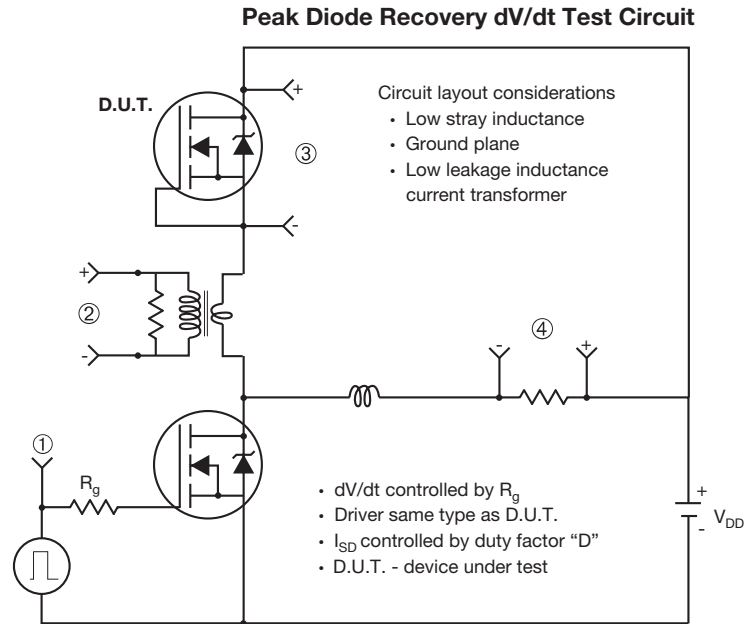


Fig. 13b - Gate Charge Test



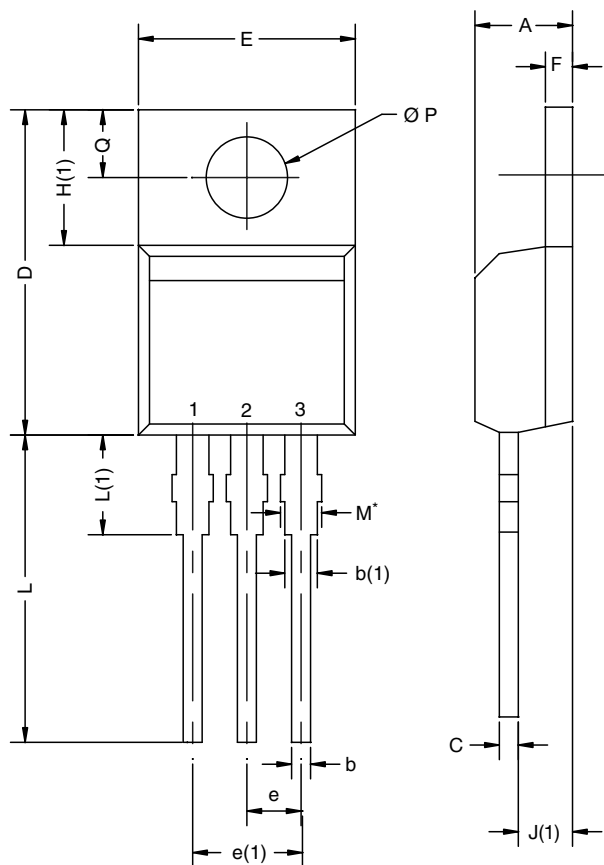
**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?91120](http://www.vishay.com/ppg?91120).

## TO-220AB

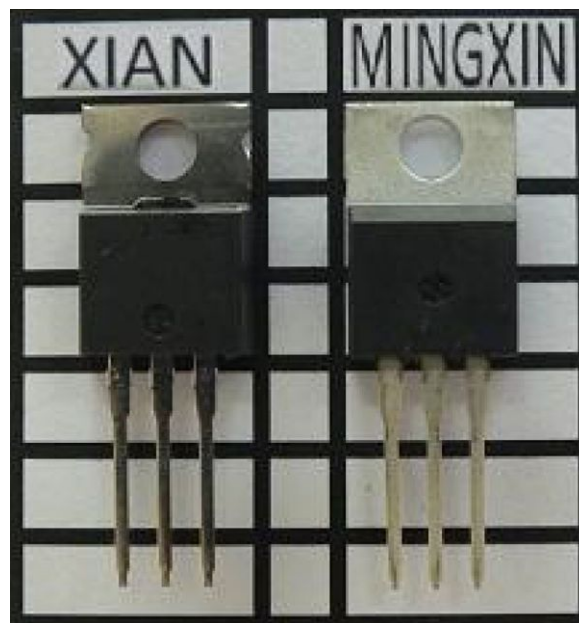


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
$\varnothing P$	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: X12-0208-Rev. N, 08-Oct-12  
DWG: 5471

### Notes

- \* M = 1.32 mm to 1.62 mm (dimension including protrusion)  
Heatsink hole for HVM
- Xi'an and Mingxin actual photo







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